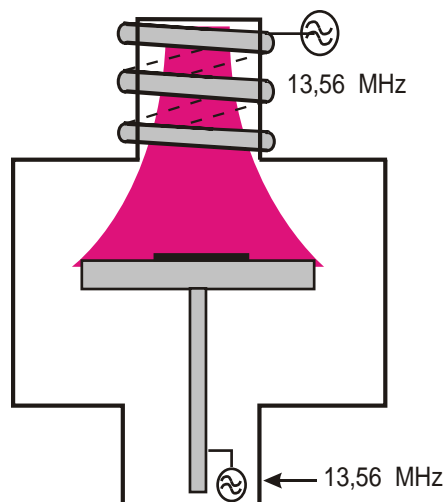
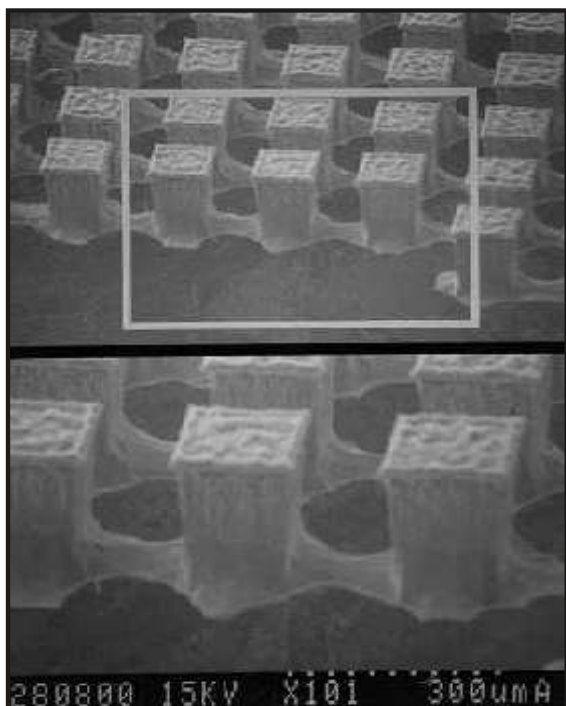


Plasmalab Data

100 μm deep anisotropic GaAs ICP-RIE



Courtesy of Siemens Munich ZFE T KM 3 (Dr G Franz):
95 μm deep anisotropic GaAs (resist mask)

Plasmalab 80 Plus

Plasmalab System 133



Technology:

Inductive Coupled Plasma ICP-RIE*
13 MHz induced RF bias
 BCl_3/Cl_2 process

*original work by ECR, see:
http://www.oxfordplasma.de/technols/rie_ecr.htm

Results:

etch rate: 1.0 - 1.1 $\mu\text{m}/\text{min}$
smoother walls at lower rates
mask: trilevel photoresist (AZ 4562)
uniformity: $\pm 1\%$ ($2''$)

Plasmalab System 100